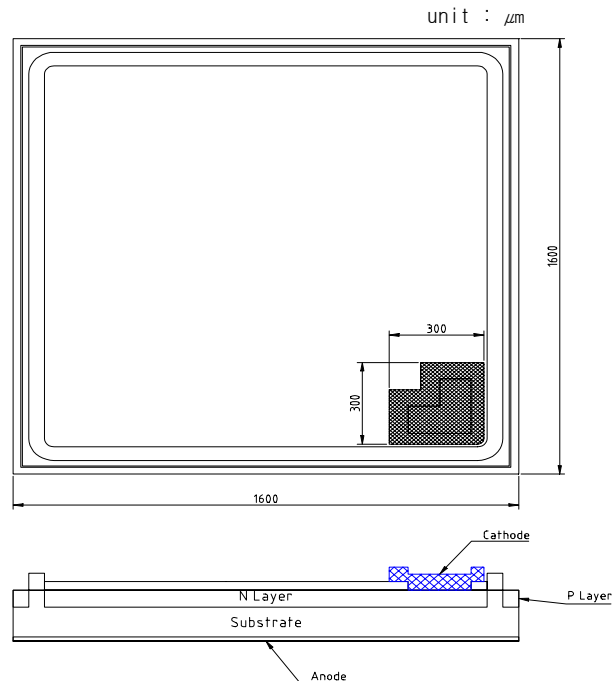


1. Structure

- 1.1 Chip Size : 1.60mm X 1.60mm
- 1.2 Chip Thickness : $400 \pm 20 \mu\text{m}$
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Cathode(Top) : $300 \mu\text{m} \times 300 \mu\text{m}$
 - Anode(Bottom)
- 1.6 Active Area : $1.40 \text{mm} \times 1.40 \text{mm}$



2. Electrical-Optical Characteristics

($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Open Circuit Voltage	V_{OP}	-0.3	-0.32		V	Note(1)
Short Circuit Current	I_{SC}	-16	-20		μA	Note(1)
Spectrum Sensitivity	λ	430~1,100			nm	
Peak Sensing Wavelength	λ_P		940		nm	
Forward Voltage	V_F	-0.5		-1.3	V	$I_F = 10 \text{mA}$
Dark Current	I_D		-5	-10	nA	$V_R = 10 \text{V}$
Reverse Breakdown Voltage	BV_R	-30			V	$I_R = 10 \mu\text{A}$

Note(1) : Parallel light of 1,000Lux illumination is applied by a Tungsten lamp of 2856k.

3. Maximum Ratings

($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse Breakdown Voltage	BV_R	-30	V
Junction Temperature	T_J	150	$^\circ\text{C}$

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